

### FEATURES

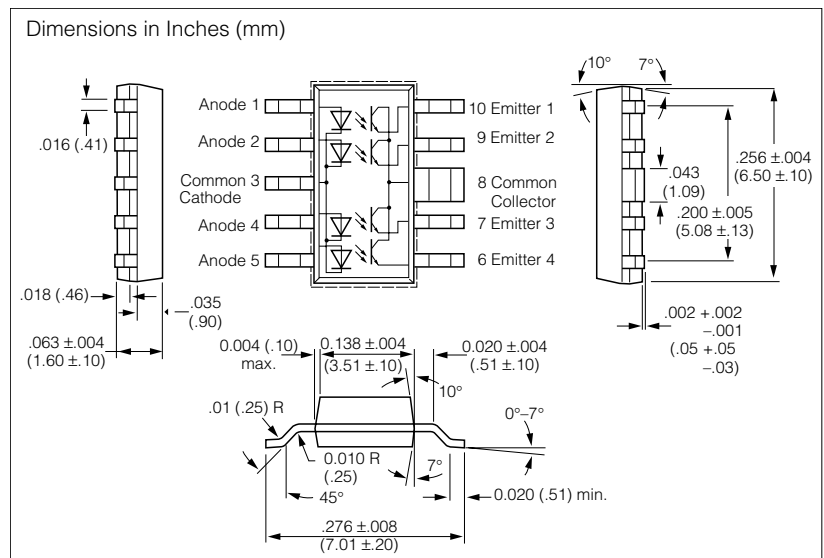
- Transistor Optocoupler in SOT223/10 Package
- End Stackable, 1.27 mm Spacing
- Low Current Input
- Very High CTR, 150% Typical at  $I_F=1$  mA,  $V_{CE}=5$  V
- Good CTR Linearity Versus Forward Current
- Minor CTR Degradation
- Field Effect Stable by TRIOS® (Transparent IOn Shield)
- High Collector-Emitter Voltage,  $V_{CEO}=70$  V
- Low Coupling Capacitance
- High Common Mode Transient Immunity
- Isolation Test Voltage: 1768  $V_{RMS}$

### APPLICATIONS

- Telecommunication
- SMT
- PCMCIA
- Instrumentation

### DESCRIPTION

The SFH6943 is a four channel mini-optocoupler suitable for high density packaged PCB application. It has a minimum of 1768  $V_{RMS}$  isolation from input to output. The device consists of four phototransistors as detectors. Each channel is individually controlled. The optocoupler is housed in a SOT223/10 package. All the cathodes of the input LEDs and all the collectors of the output transistors are commoned enabling a pin count reduction from 16 pins to 10 pins—a significant space savings as compared to four channels that are electrically isolated individually.



### Absolute Maximum Ratings

#### Emitter(GaAlAs)

Reverse Voltage	.....	.3 V
DC Forward Current	.....	5 mA
Surge Forward Current ( $t_P \leq 10 \mu s$ )	.....	100 mA
Total Power Dissipation	.....	10 mW

#### Detector (Si Phototransistor)

Collector-Emitter Voltage	.....	70 V
Emitter-Collector Voltage	.....	7 V
Collector Current	.....	10 mA
Surge Collector Current ( $t_P < 1$ ms)	.....	20 mA
Total Power Dissipation	.....	20 mW

#### Package Insulation

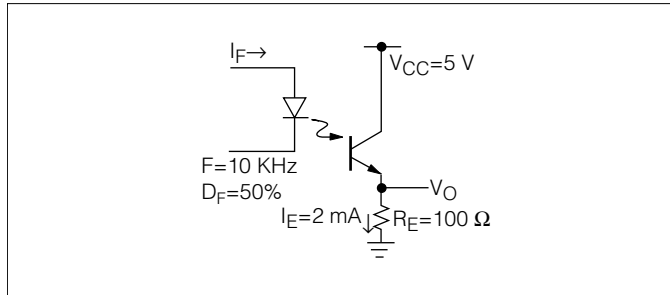
Isolation Test Voltage (between emitter and detector, refer to climate DIN 40046, part 2, Nov. 74), $t=1$ sec.	.....	1768 $V_{RMS}$
Creepage	.....	$\geq 4$ mm
Clearance	.....	$\geq 4$ mm
Comparative Tracking Index per DIN IEC 112/VDE0303, part 1	.....	175
Isolation Resistance		
$V_{IO}=100$ V, $T_A=25^\circ C$	.....	$\geq 10^{11} \Omega$
$V_{IO}=100$ V, $T_A=100^\circ C$	.....	$\geq 10^{10} \Omega$
Storage Temperature Range	.....	-55 to +150°C
Ambient Temperature Range	.....	-55 to +100°C
Junction Temperature	.....	100°C
Soldering Temperature ( $t=10$ sec. max.)		
Dip soldering plus reflow soldering processes	.....	260°C

**Characteristics** ( $T_A=25^\circ\text{C}$ , unless otherwise specified)

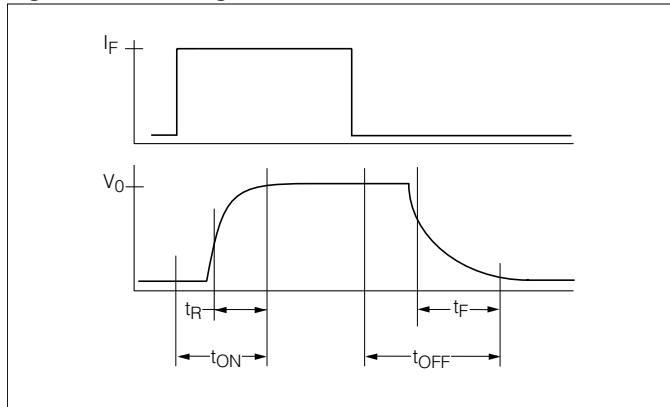
Description	Symbol	Min.	Typ.	Max.	Unit
<b>Emitter (IR GaAs)</b>					
Forward Voltage, $I_F=5\text{ mA}$	$V_F$	—	1.25	—	V
Reverse Current, $V_R=3\text{ V}$	$I_R$	—	0.01	10	$\mu\text{A}$
Capacitance, $V_R=0\text{ V}$ , $f=1\text{ MHz}$	$C_0$	—	5	—	pF
Thermal Resistance	$R_{thJA}$	—	1000	—	K/W
<b>Detector (Si Phototransistor)</b>					
Collector-Emitter Voltage, $I_{CE}=10\ \mu\text{A}$	$V_{CEO}$	70	—	—	V
Emitter-Collector Voltage, $I_{EC}=10\ \mu\text{A}$	$V_{ECO}$	7	—	—	V
Capacitance, $V_{CE}=5\text{ V}$ , $f=1\text{ MHz}$	$C_{CE}$	—	6	—	pF
Thermal Resistance	$R_{thJA}$	—	500	—	K/W
<b>Package</b>					
Coupling Capacitance	$C_C$	—	1	—	pF

Description	Symbol	-2	-3	-4	Unit	Condition
Coupling Transfer Ratio	$I_E/I_F$	63–200	100–320	160–500	%	$I_F=1\text{ mA}$ , $V_{CE}=1.5\text{ V}$
Coupling Transfer Ratio	$I_E/I_F$	typ, 100 ( $\geq 32$ )	typ, 160 ( $\geq 50$ )	typ, 250 ( $\geq 80$ )	%	$I_F=0.5\text{ mA}$ , $V_{CC}=5\text{ V}$
Collector-Emitter Leakage Current	$I_{CEO}$	50	50	50	nA	$V_{CE}=10\text{ V}$

**Figure 1. Switching times (non-saturated), typical**

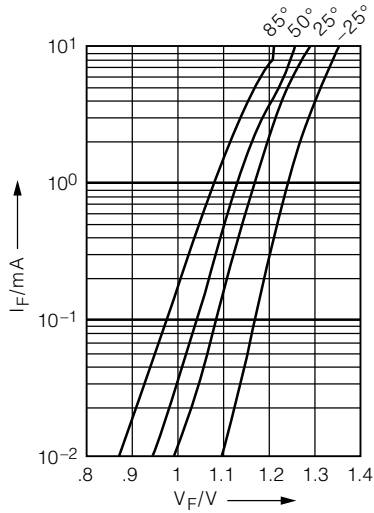


**Figure 2. Switching waveform (non-saturated)**

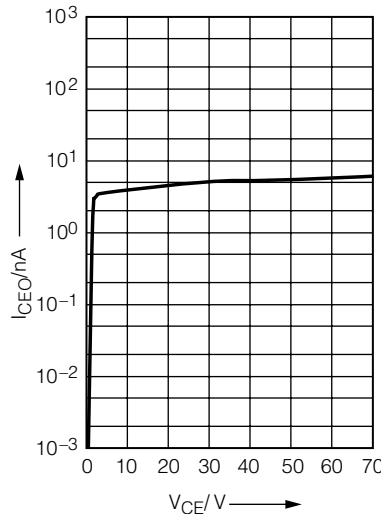


Description	Symbol	Value	Unit	Test Conditions
Turn-on Time	$t_{on}$	3	$\mu\text{s}$	$I_E=2\text{ mA}$ $R_E=100\ \Omega$ $T_A=25^\circ\text{C}$ $V_{CC}=5\text{ V}$
Rise Time	$t_r$	2.6		
Turn-off Time	$t_{off}$	3.1		
Fall Time	$t_f$	2.8		

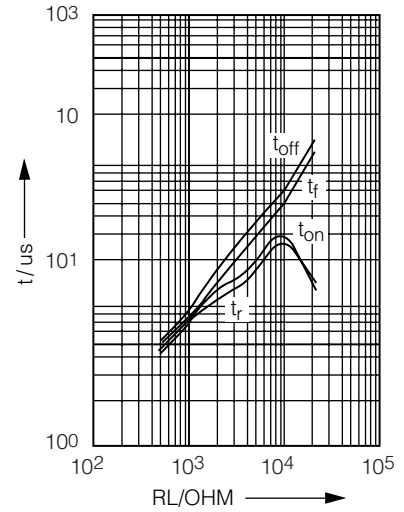
**Figure 3. LED current versus LED voltage  $V_F=f(I_F)$**



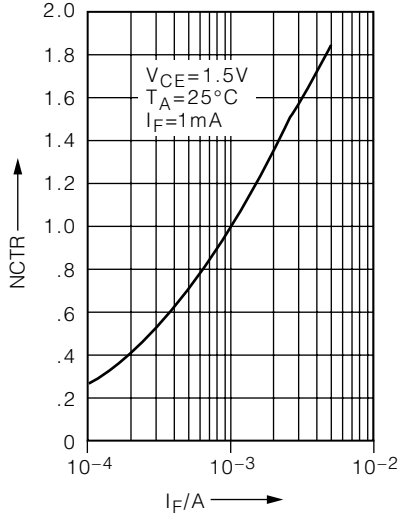
**Figure 6. Collector-emitter leakage current (typ.)  $I_{CE0}=f(V_{CE})$**



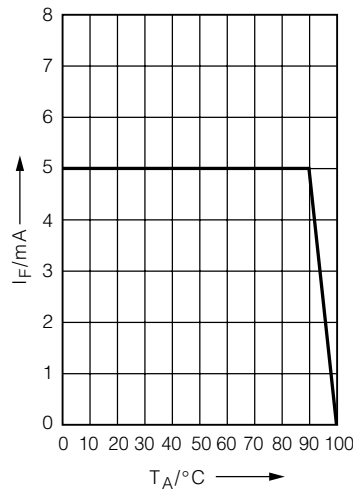
**Figure 9.  $T_A=25^\circ\text{C}$ ,  $I_F=1\text{ mA}$ ,  $V_{CC}=5\text{ V}$ ,  $t_{on}$ ,  $t_r$ ,  $t_{off}$ ,  $t_t=f(R_L)$**



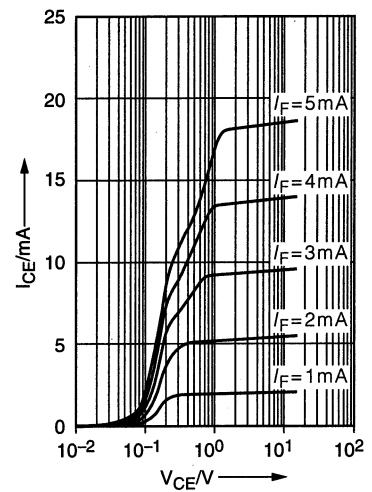
**Figure 4. Non-saturated current transfer normalized to  $I_F=1\text{ mA}$ ,  $NCTR=f(I_F)$**



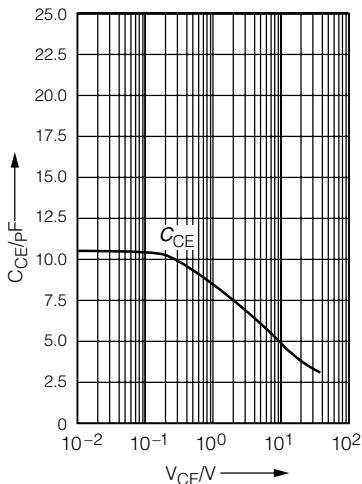
**Figure 7. Permissible forward current diode  $I_F=f(T_A=25^\circ\text{C})$**



**Figure 10. Transistor output characteristics  $T_A=25^\circ\text{C}$ ,  $I_{CE}=1\text{ (}V_{CE}, I_F\text{)}$**



**Figure 5. Transistor capacitance (typ.)  $T_A=25^\circ\text{C}$ ,  $f=1\text{ MHz}$ ,  $C_{CE}=f(V_{CE})$**



**Figure 8. Permissible power dissipation  $P_{tot}=f(T_A)$**

